

General Description

- DCX4710H is best suited for applications where the load needs to be turned on and off using micro-controllers, comparators or other control circuits particularly at a point of load. It features a discrete pre-biased PNP transistor which can support continuous maximum current of 100 mA. It also contains a pre-biased NPN transistor which can be used as a control and can be biased using a higher supply. The component devices can be used as a part of circuit or as stand alone discrete devices.

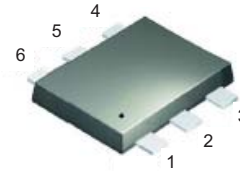


Fig. 1: SOT-563

Features

- Built in Biasing Resistors
- Epitaxial Planar Die Construction
- Ideally Suited for Automated Assembly Processes
- Lead Free By Design/ROHS Compliant (Note 1)**
- "Green" Device (Note 2)**

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. "Green Molding" Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Fig. 2
- Terminals: Finish - Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking & Type Code Information: See Page 7
- Ordering Information: See Page 7
- Weight: 0.005 grams (approximate)

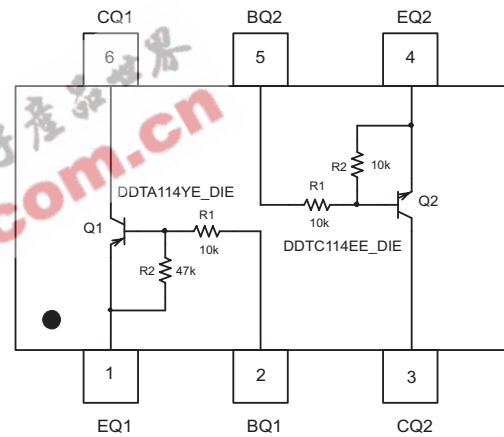


Fig. 2: Schematic and Pin Configuration

Sub-Component P/N	Reference	Device Type	R1 (NOM)	R2 (NOM)	Figure
DDTA114YE_DIE	Q1	PNP	10KΩ	47KΩ	2
DDTC114EE_DIE	Q2	NPN	10KΩ	10KΩ	2

Maximum Ratings: Total Device @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	P _d	150	mW
Power Derating Factor above 45°C	P _{der}	1.43	mW/°C
Output Current	I _{out}	100	mA

Thermal Characteristics @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Junction Operation and Storage Temperature Range	T _j , T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Ambient Air (Note 3) (Equivalent to one heated junction of PNP transistor)	R _{θJA}	833	°C/W

- Notes:
- No purposefully added lead.
 - Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 - Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; as per Diodes Inc. suggested pad layout document AP02001 on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.

Sub-Component Device - Pre-Biased PNP Transistor (Q1) @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	-50	V
Collector-Emitter Voltage	V _{CEO}	-50	V
Supply Voltage	V _{CC}	-50	V
Input Voltage	V _{IN}	+6 to -40	V
Output Current (dc)	I _{C(max)}	-100	mA

Sub-Component Device - Pre-Biased PNP Transistor (Q1) @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CB0}	50	V
Collector-Emitter Voltage	V _{CEO}	50	V
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-10 to +40	V
Output Current (dc)	I _{C(max)}	100	mA

Electrical Characteristics: Pre-Biased PNP Transistor (Q1) @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Cut Off Current	I _{CB0}	—	—	-100	nA	V _{CB} = -50V, I _E = 0
Collector-Emitter Cut Off Current	I _{CEO}	—	—	-1	μA	V _{CE} = -50V, I _B = 0
Emitter-Base Cut Off Current	I _{EBO}	—	—	-500	μA	V _{EB} = -5V, I _C = 0
Collector-Base Breakdown Voltage	V _{(BR)CB0}	-50	—	—	V	I _C = -10 μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-50	—	—	V	I _C = -2 mA, I _B = 0
Output Off Voltage	V _{OH}	-4.6	—	—	V	V _{CC} = -5V, V _B = -0.05V, R _L = 1KΩ
Input Off Voltage	V _{I(OFF)}	—	-0.71	-0.5	V	V _{CE} = -5V, I _C = -100μA
Output Off Current	I _{O(OFF)}	—	—	-1	μA	V _{CC} = -50V, V _I = 0V
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.066	-0.1	V	I _C = 5 mA, I _B = -0.25 mA
		—	-0.078	-0.1		I _C = -10mA, I _B = -0.3mA
		—	-0.06	-0.1		I _C = -10mA, I _B = -1mA
		—	-0.04	-0.1		I _C = -10mA, I _B = -5mA
		—	-0.99	-1.15		I _C = -100mA, I _B = -5mA
		—	0.99	-1.15		I _C = -100mA, I _B = -10mA
Equivalent on-resistance*	R _{CE(SAT)}	—	—	3.5	Ω	I _C = -100mA, I _B = -10mA
DC Current Gain	h _{FE}	50	—	—	—	V _{CE} = -5V, I _C = -1 mA
		130	—	—	—	V _{CE} = -5V, I _C = -5 mA
		180	—	—	—	V _{CE} = -5V, I _C = -50 mA
		100	—	—	—	V _{CE} = -5V, I _C = -100 mA
		140	—	—	—	V _{CE} = -10V, I _C = -5 mA
Output On Voltage	V _{OL}	—	-0.185	-0.22	V	V _{CC} = -5V, V _B = -2.5V, R _L = 1KΩ
Input On Voltage (Load is on)	V _{I(ON)}	-1.25	-0.9	—	V	V _O = -0.3V, I _C = -2 mA
Input Current	I _i	—	—	-0.88	mA	V _I = -5V
Base-Emitter Turn-on Voltage	V _{BE(ON)}	—	-0.72	-0.8	V	V _{CE} = -5V, I _C = 100μA
Base-Emitter Saturation Voltage	V _{BE(SAT)}	—	-1.15	-1.25	V	I _C = 1mA, I _B = 50μA
Input Resistor +/- 30% (Base)	ΔR1	7	10	13	KΩ	—
Pull-up Resistor (Base to V _{CC} supply)	R2	32	47	62	KΩ	—
Resistor Ratio	Δ(R2/R1)	20	—	20	%	—

Electrical Characteristics: Pre-Biased PNP Transistor (Q1) (Continued)

SMALL SIGNAL CHARACTERISTICS						
Transition Frequency (gain bandwidth product)	f_T	—	200	—	MHz	$V_{CE} = -10V, I_E = -5mA, f = 100MHz$
Collector capacitance (C _{cb} -Output Capacitance)	C_C	—	5	—	pF	$V_{CB} = -10V, I_E = 0A, f = 1MHz$

*Pulse Test: Pulse width, $t_p < 300 \mu s$, Duty Cycle, $d < 0.02$

Pre-Biased NPN Transistor (Q2) @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Cut Off Current	I_{CBO}	—	—	100	nA	$V_{CB} = 50V, I_E = 0$
Collector-Emitter Cut Off Current	I_{CEO}	—	—	1	μA	$V_{CE} = 50V, I_B = 0$
Emitter-Base Cut Off Current	I_{EBO}	—	—	500	μA	$V_{EB} = 5V, I_C = 0$
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	50	—	—	V	$I_C = 10 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 2 mA, I_B = 0$
Output Off Voltage	V_{OH}	4.6	—	—	V	$V_{CC} = 5V, V_B = 0.05V, R_L = 1K\Omega$
Input Off Voltage	$V_{I(OFF)}$	—	1.2	0.8	V	$V_{CE} = 5V, I_C = 100\mu A$
Output Current	$I_{O(OFF)}$	—	—	1	μA	$V_{CC} = 50V, V_I = 0V$
ON CHARACTERISTICS						
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.06	0.1	V	$I_C = 5 mA, I_B = 0.25 mA$
		—	0.06	0.1		$I_C = 10mA, I_B = 0.5mA$
		—	0.042	0.06		$I_C = 10mA, I_B = 1mA$
		—	0.026	0.04		$I_C = 10mA, I_B = 5mA$
		—	0.272	0.35		$I_C = 100mA, I_B = 5mA$
		—	0.28	0.35		$I_C = 100mA, I_B = 10mA$
Equivalent on-resistance*	$R_{CE(SAT)}$	—	—	3.5	Ω	$I_C = 100mA, I_B = 10mA$
DC Current Gain	h_{FE}	12	—	—	—	$V_{CE} = 5V, I_C = 1 mA$
		45	—	—	—	$V_{CE} = 5V, I_C = 5 mA$
		130	—	—	—	$V_{CE} = 5V, I_C = 50 mA$
		70	—	—	—	$V_{CE} = 5V, I_C = 100 mA$
		40	58	—	—	$V_{CE} = 10V, I_C = 5 mA$
Output On Voltage	V_{OL}	—	0.12	0.2	V	$V_{CC} = 5V, V_B = 2.5V, R_L = 1K\Omega$
Input On Voltage	$V_{I(ON)}$	2.8	1.6	—	V	$V_O = 0.3V, I_C = 2 mA$
Input Current	I_i	—	—	0.88	mA	$V_I = 5V$
Base-Emitter Turn-on Voltage	$V_{BE(ON)}$	—	—	1.195	V	$V_{CE} = 5V, I_C = 100\mu A$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	—	1.02	V	$I_C = 1mA, I_B = 50\mu A$
Input Resistor +/- 30% (Base)	R1	7	10	13	K Ω	—
Resistor Ratio	(R2/R1)	0.8	1	1.2	—	—
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency (Gain bandwidth product)	f_T	—	250	—	MHz	$V_{CE} = 10V, I_E = 5mA, f = 100MHz$
Collector capacitance (C _{cb} -Output Capacitance)	C_C	—	4	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

*Pulse Test: Pulse width, $t_p < 300 \mu s$, Duty Cycle, $d < 0.02$

Typical Characteristics @ $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified

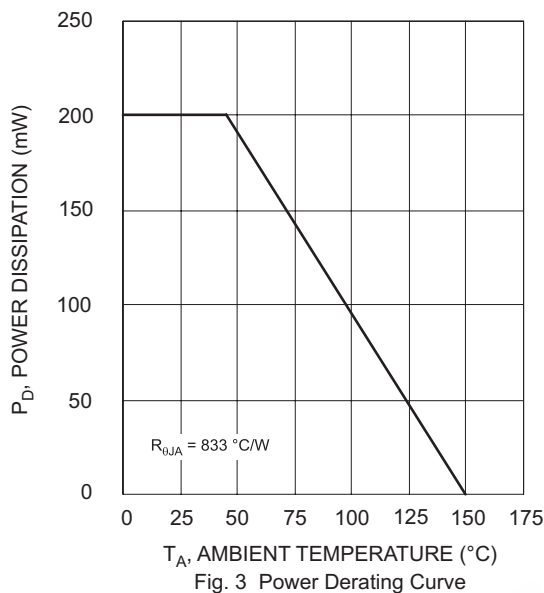


Fig. 3 Power Derating Curve

Characteristics Curves of PNP Transistor (Q1) @ $T_{amb} = 25^{\circ}\text{C}$ unless otherwise specified

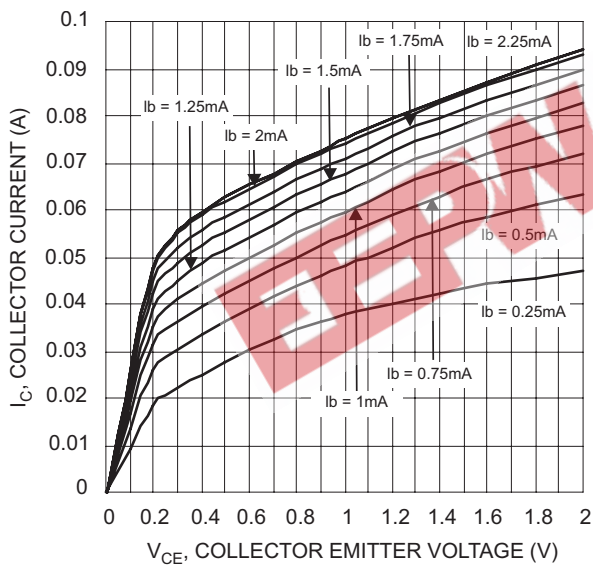


Fig. 4 V_{CE} vs. I_C

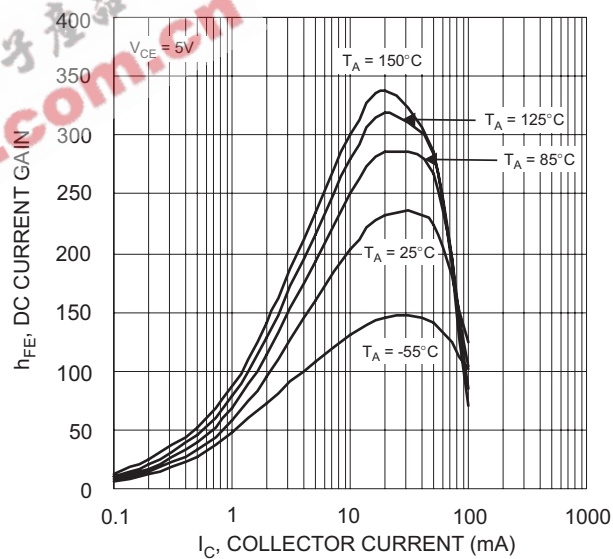


Fig. 5 DC Current Gain vs. I_C

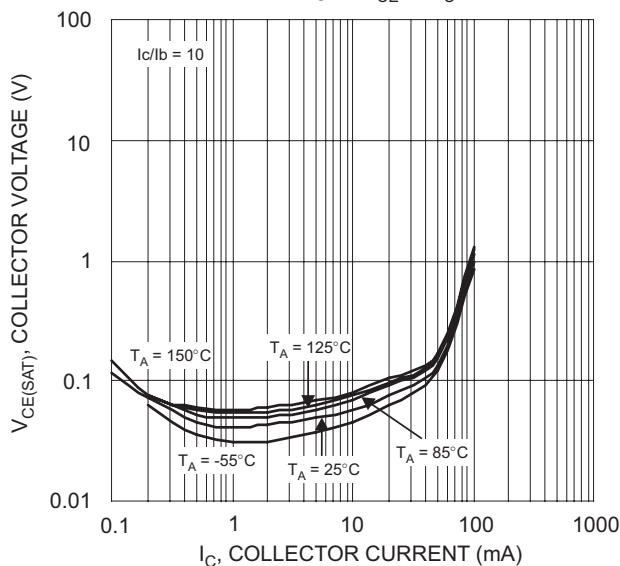


Fig. 6 I_C vs. $V_{CE(SAT)}$

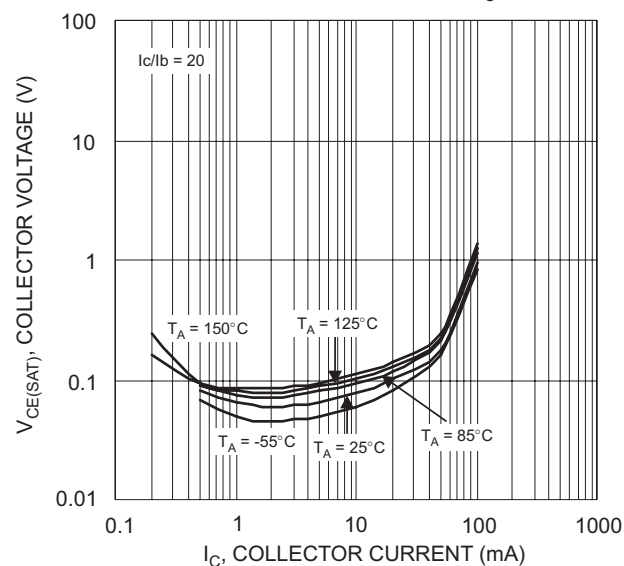


Fig. 7 I_C vs. $V_{CE(SAT)}$

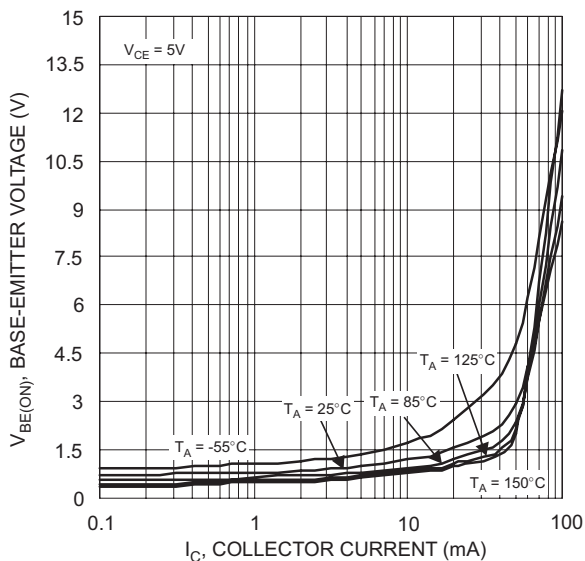


Fig. 8 I_C vs. $V_{BE(ON)}$

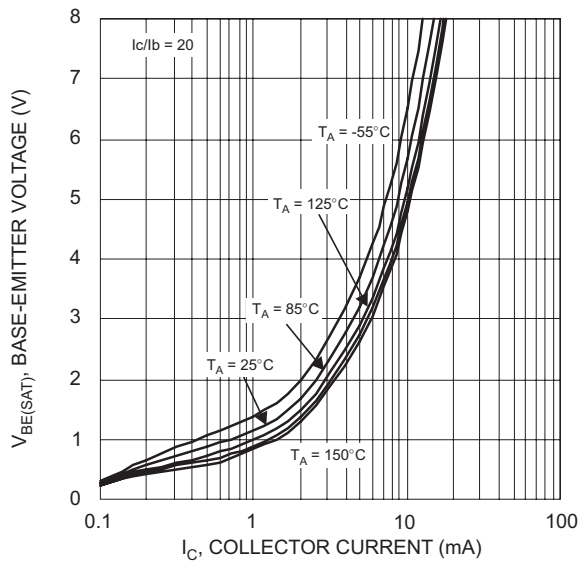


Fig. 9 I_C vs. $V_{BE(SAT)}$

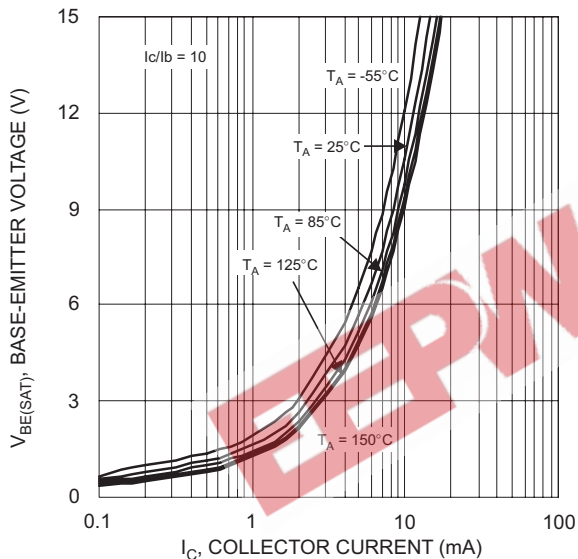


Fig. 10 I_C vs. $V_{BE(SAT)}$

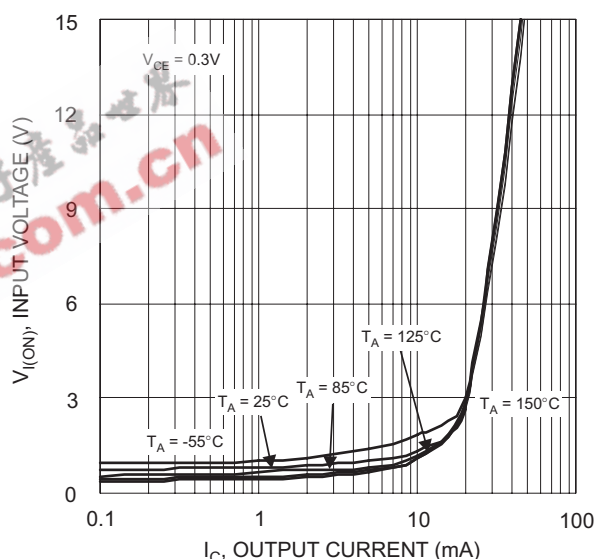


Fig. 11 Input Voltage vs. Collector Current

Characteristics Curves of NPN Transistor (Q2) @ $T_{amb} = 25^\circ C$ unless otherwise specified

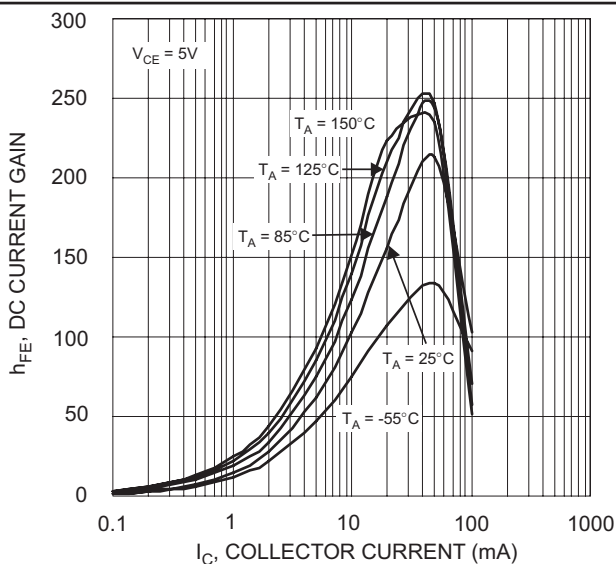


Fig. 12 DC Current Gain vs. I_C

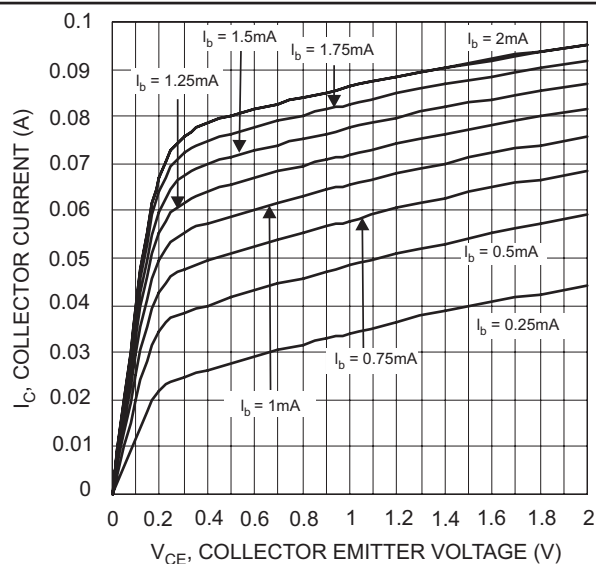


Fig. 13 V_{CE} vs. I_C

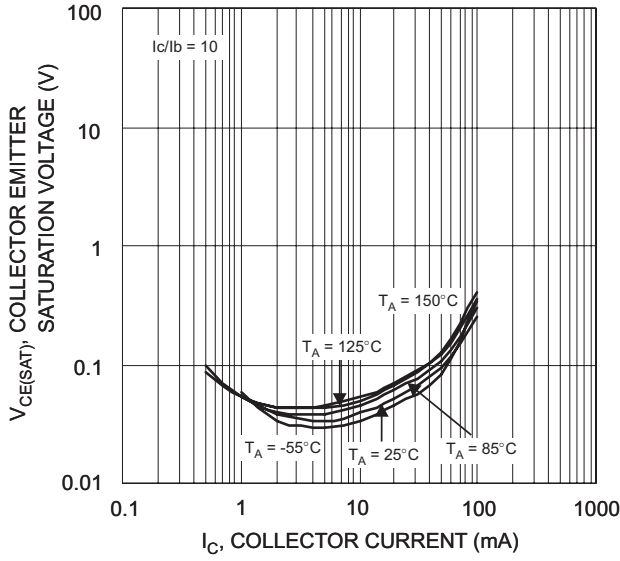


Fig. 14 I_C vs. $V_{CE(SAT)}$

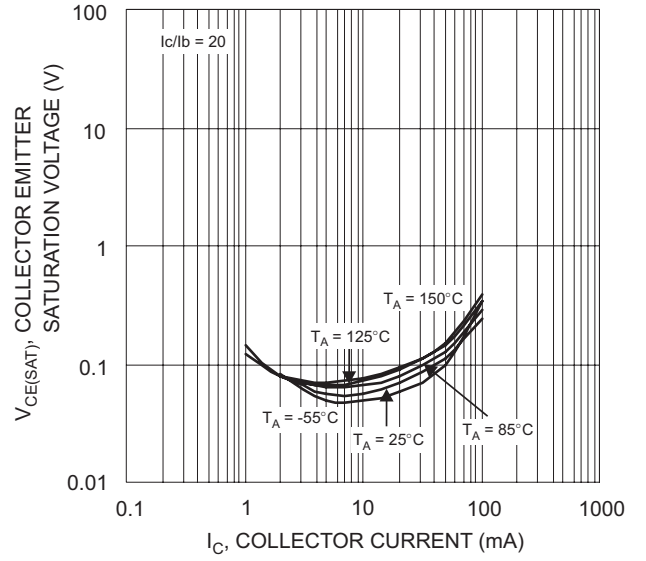


Fig. 15 I_C vs. $V_{CE(SAT)}$

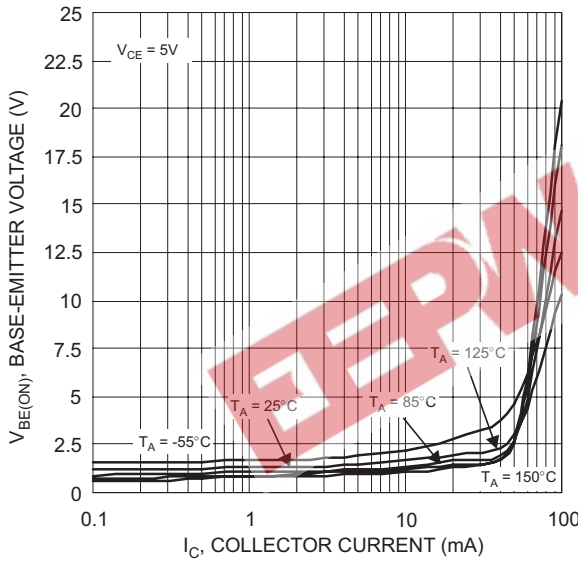


Fig. 16 I_C vs. $V_{BE(ON)}$

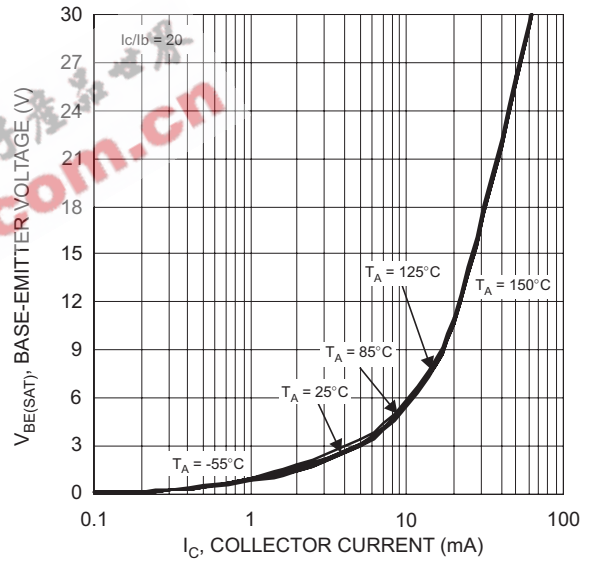


Fig. 17 I_C vs. $V_{BE(SAT)}$

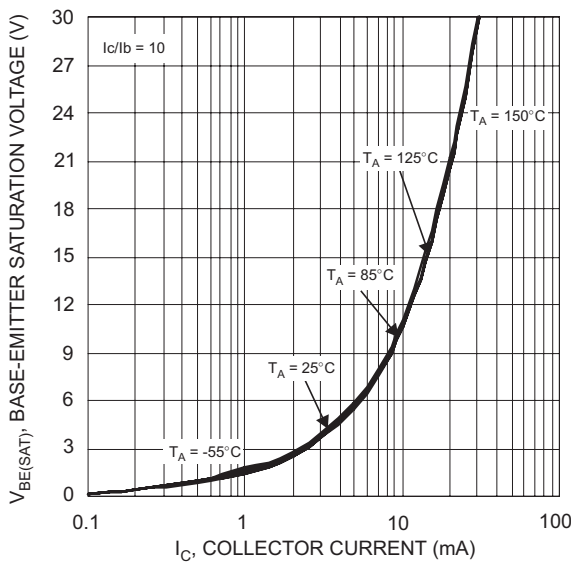


Fig. 18 I_C vs. $V_{BE(SAT)}$

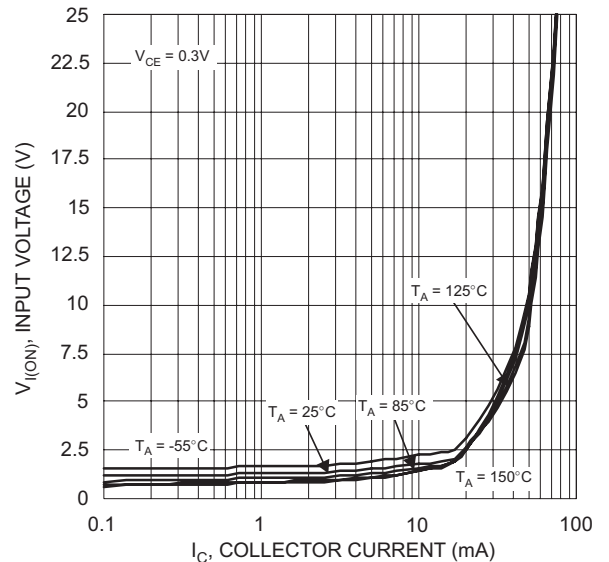


Fig. 19 Input Voltage vs. Output Current

Ordering Information (Note 5)

Device	Marking Code	Packaging	Shipping
DCX4710H-7	C02	SOT-563	3000/Tape & Reel

Notes: 5. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information

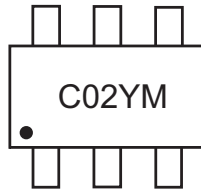
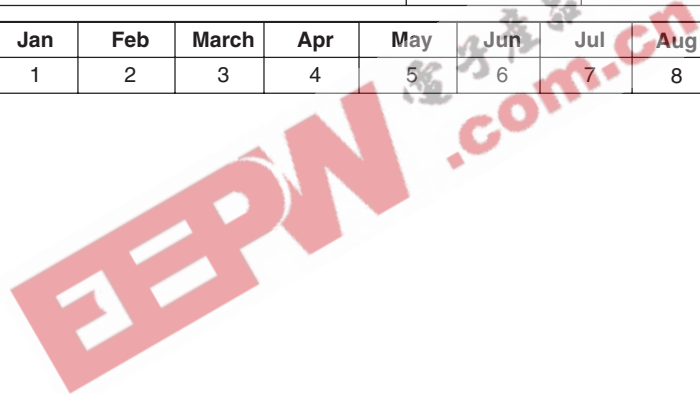


Fig. 20

C02 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year e.g., T = 2006
 M = Month e.g., 9 = September

Date Code Key

Year		2006		2007		2008		2009				
Code		T		U		V		W				
Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



Mechanical Details

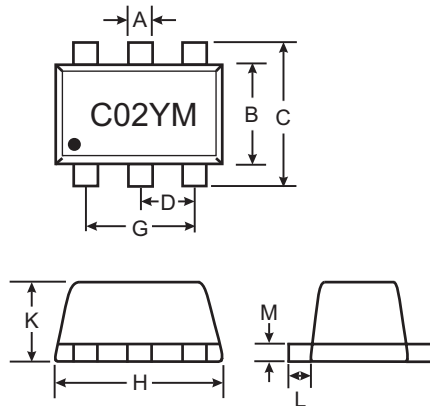


Fig. 21

SOT-563			
Dim	Min	Max	Typ
A	0.15	0.3	0.25
B	1.1	1.25	1.2
C	1.55	1.7	1.6
D	0.5		
G	0.9	1.1	1
H	1.5	1.7	1.6
K	0.56	0.6	0.6
L	0.15	0.25	0.2
M	0.1	0.18	0.11
All Dimensions in mm			

Suggested Pad Layout: (Based on IPC-SM-782)

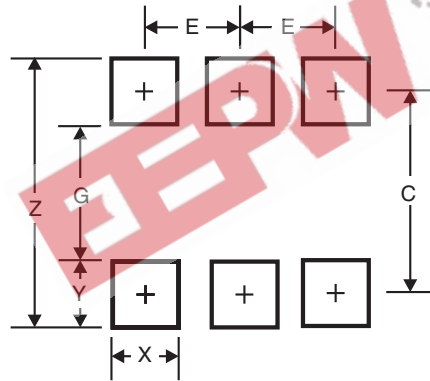


Fig. 22

Figure 4 Dimensions	SOT-563
Z	2.2
G	1.2
X	0.375
Y	0.5
C	1.7
E	0.5

IMPORTANT NOTICE

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